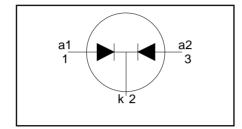
PBYR7025WT series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 20 \text{ V} / 25 \text{ V}$$
 $I_{O(AV)} = 70 \text{ A}$
 $V_F \le 0.46 \text{ V}$

GENERAL DESCRIPTION

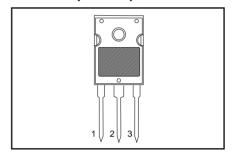
Dual, common cathode schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR7025WT series is supplied in the conventional leaded SOT429 (TO247) package.

PINNING

PIN	DESCRIPTION		
1	anode 1 (a)		
2	cathode (k)		
3	anode 2 (a)		
tab	cathode		

SOT429 (TO247)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	. MAX.		UNIT
V _{RRM} V _{RWM} V _R	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage	T _{mb} ≤ 116 °C		-20 20 20 20	-25 25 25 25	<<<
I _{O(AV)}	Average output current (both diodes conducting)	square wave; $\delta = 0.5$; $T_{mb} \le 114 ^{\circ}\text{C}$	-	7	0	А
I _{FRM}	Repetitive peak forward current per diode	$t = 25 \mu s$; δ = 0.5; $T_{mb} \le 114 ^{\circ} C$	-	7	0	Α
I _{FSM}	Non-repetitive peak forward current, per diode	t = 10 ms t = 8.3 ms sinusoidal T _i = 125 °C prior to surge; with reapplied V_{RRM_i}	-		00 50	A
I _{RRM}	Repetitive peak reverse current per diode	$t_{p} = 2 \mu s; \delta = 0.001$	-	2	2	Α
I _{RSM}	Non-repetitive peak reverse current per diode	$t_{p} = 100 \ \mu s$	-	2	2	Α
$egin{array}{c} T_{stg} \ T_{j} \end{array}$	Storage temperature Operating junction temperature		-65 -		50 50	သို့ (C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th j-mb}}$ $R_{\text{th j-a}}$	mounting base	per diode both diodes in free air		- - 45	0.9 0.65 -	K/W K/W

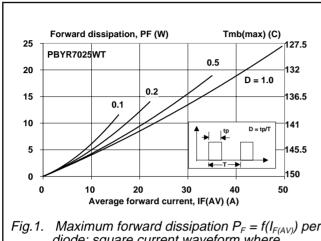
PBYR7025WT series

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

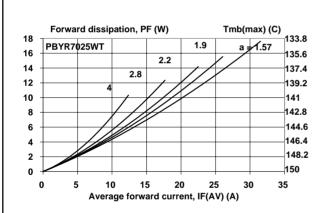
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage (per diode)	I _F = 35 A; T _j = 125°C I _F = 70 A; T _j = 125°C	-	0.40	0.46	V
		$I_F = 70 \text{ A}, I_j = 125 \text{ C}$ $I_F = 70 \text{ A}$	-	0.52 0.58	0.54 0.64	V
I _R	Reverse current (per diode)	$V_R = V_{RRM}$	-	0.8 40	15 120	mA mA
C _d	Junction capacitance (per diode)	$V_R = V_{RRM}^{\text{Norm}}$; $T_j = 100 ^{\circ}\text{C}$ $f = 1\text{MHz}$; $V_R = 5\text{V}$; $T_j = 25 ^{\circ}\text{C}$ to 125 $^{\circ}\text{C}$	-	2100	-	pF

PBYR7025WT series



Reverse Current, IR (mA) PBYR7025WT 1000 100 Tj =125C 10 Tj =100C Tj =75C Tj =50C Tj =25C 0.01 10 15 20 Reverse Voltage, VR (V) Fig.4. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_i

Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.



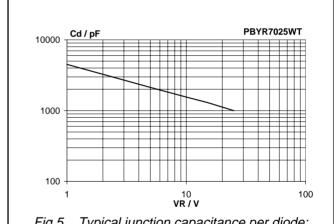
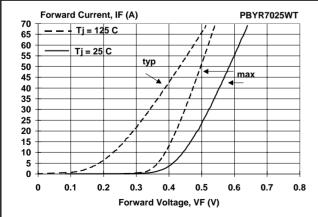


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where $a = f(I_{F(AV)})$ $factor = I_{F(RMS)} / I_{F(AV)}$.

Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 150 °C.



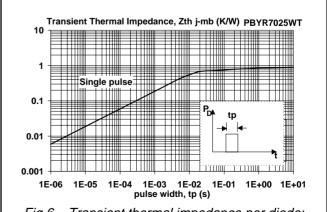
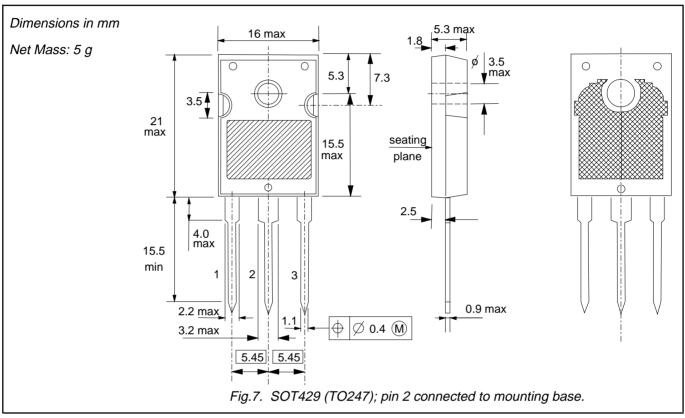


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

Fig.6. Transient thermal impedance per diode; $Z_{th j-mb} = f(t_p).$

PBYR7025WT series

MECHANICAL DATA



- Refer to mounting instructions for SOT429 envelope.
 Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier diodes Schottky barrier

PBYR7025WT series

DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification This data sheet contains preliminary data; supplementary data may be published lat					
Product specification	This data sheet contains final product specifications.				
Limiting values					

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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